

STN851

Low voltage fast-switching NPN power transistor

Features

- Very low collector to emitter saturation voltage
- High current gain characteristic
- Fast-switching speed

Applications

- Emergency lighting
- Voltage regulators
- Relay drivers
- High efficiency low voltage switching applications

Description

The device is manufactured in Planar Technology with "Base Island" layout.

The resulting transistor shows exceptional high gain performance coupled with very low saturation voltage.

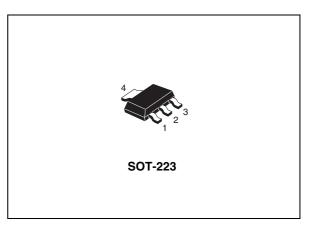


Figure 1. Internal schematic diagram

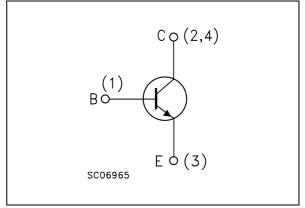


Table 1. Device summary

Order code	Marking	Marking Package Packaging	
STN851	N851	SOT-223	Tape and reel

1 Electrical ratings

Table 2.	Absolute maximum ratings
Table 2.	Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	150	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	60	V
V _{EBO}	Emitter-base voltage (I _C = 0)	7	V
۱ _C	Collector current	5	А
I _{CM}	Collector peak current (t _P < 5 ms)	10	А
Ι _Β	Base current	1	А
I _{BM}	Base peak current (t _P < 5 ms)	2	А
P _{tot}	Total dissipation at T _{amb} = 25 °C	1.6	W
T _{stg}	Storage temperature	-65 to 150	°C
ТJ	Max. operating junction temperature	150	°C

Table 3.Thermal data

Symbol	Parameter	Value	Unit
R _{thj-amb}	Thermal resistance junction-ambient ⁽¹⁾	78	°C/W

1. Device mounted on a p.c.b. area of 1 \mbox{cm}^2



2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Table 4. Electrical characteristics							
Symbol	mbol Parameter Test conditions		onditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current $(I_E = 0)$	V _{CB} = 120 V V _{CB} = 120 V	T _c = 100 °C			50 1	nΑ μΑ
I _{EBO}	I_{EBO} Emitter cut-off current ($I_C = 0$)					10	nA
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = 100 μA		150			v
V _{(BR)CEO} ⁽¹⁾	$V_{(BR)CEO}^{(1)}$ Collector-emitter breakdown voltage $(I_B = 0)$			60			v
V _{(BR)EBO}	V _{(BR)EBO} Emitter-base breakdown voltage (I _C = 0)			7			v
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	$I_C = 100 \text{ mA}$ $I_C = 1 \text{ A}$ $I_C = 2 \text{ A}$ $I_C = 5 \text{ A}$	I _B = 50 mA		10 70 140 320	50 120 250 500	mV mV mV mV
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	I _C = 4 A	l _B = 200 mA		1	1.15	v
V _{BE(on)} ⁽¹⁾	Base-emitter on voltage	$I_{\rm C} = 4$ A	$V_{CE} = 1 V$		0.89	1	V
h _{FE} ⁽¹⁾	DC current gain	$I_{C} = 10 \text{ mA}$ $I_{C} = 2 \text{ A}$ $I_{C} = 5 \text{ A}$ $I_{C} = 10 \text{ A}$	$V_{CE} = 1 V$ $V_{CE} = 1 V$	150 150 90 30	300 270 140 50	350	
f _T	Transition frequency	V _{CE} = 10 V	I _C = 100 mA		130		MHz
C _{CBO}	Collector-base capacitance (I _E = 0)	V _{CB} = 10 V	f = 1 MHz		50		pF
t _{on} t _s t _f	Resistive load Turn-on time Storage time Fall time	I _C = 1 A I _{B1} = -I _{B2} = 0.	V _{CC} = 10 V 1 A		50 1.35 120		ns µs ns

 Table 4.
 Electrical characteristics

1. Pulse duration = 300 $\mu s,$ duty cycle $\leq 1.5\%$



Figure 2.

2.1 Electrical characteristics (curves)

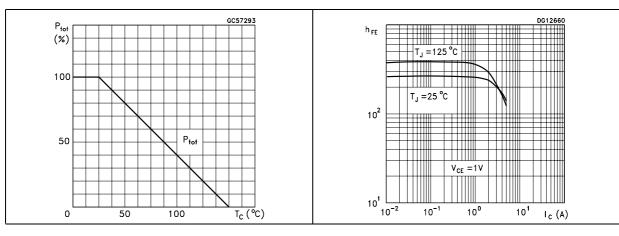


Figure 3.

Figure 5.

DC current gain

Collector-emitter saturation

Figure 4. Collector-emitter saturation voltage

Derating curve

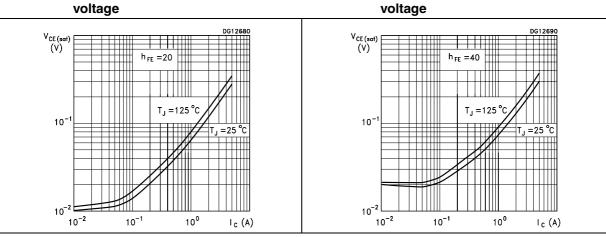
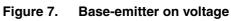
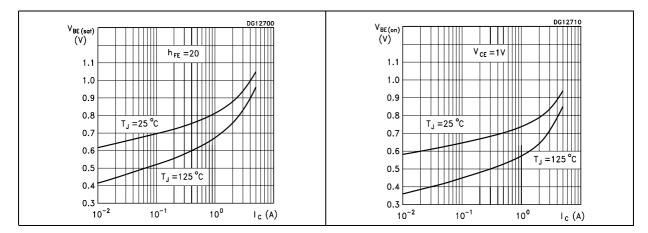


Figure 6. Base-emitter saturation voltage







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DG12730 $t_{s}(ns)$ 2500 $V_{cc} = 10V$ $V_{BB(off)} = -5V$ $I_{B(on)} = -I_{B(off)}$ $h_{FE} = 10$ 2000 t_(on)=300µs 1500 1000 500 L 0 0.5 1.5 2 2.5 I_C (A) 1

Figure 8. Resistive load switching time



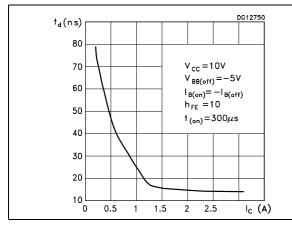


Figure 12. Inductive load switching time

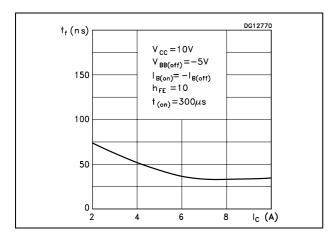


Figure 9. Resistive load switching time

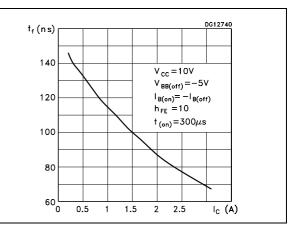
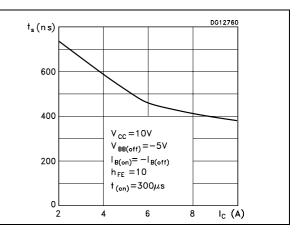


Figure 11. Inductive load switching time



2.2 Test circuit

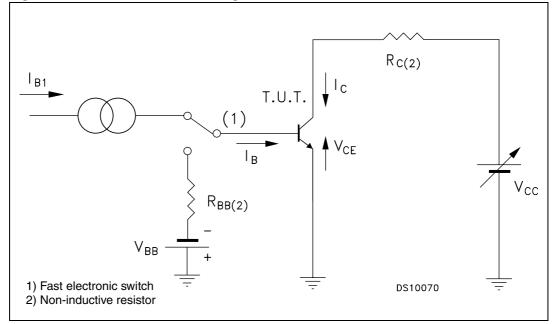


Figure 13. Resistive load switching test circuit

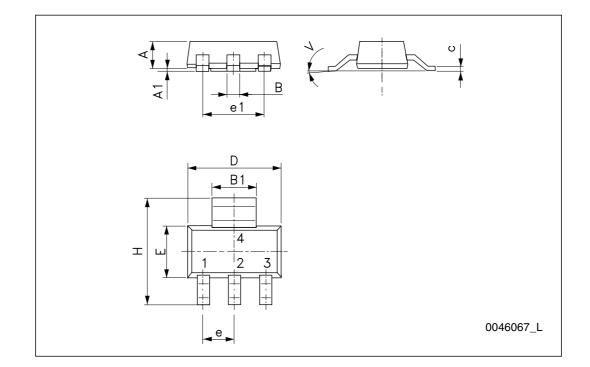


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and products status are available at: www.st.com. ECOPACK is an ST trademark.



	SOT-223 mechanical data					
DIM.	mm.					
	min.	typ	max.			
А			1.80			
A1	0.02		0.1			
В	0.60	0.70	0.85			
B1	2.90	3.00	3.15			
с	0.24	0.26	0.35			
D	6.30	6.50	6.70			
е		2.30				
e1		4.60				
E	3.30	3.50	3.70			
н	6.70	7.00	7.30			
V			10 °			





4 Revision history

Table 5.Document revision history

	Date	Revision	Changes
09	-Sep-2003	6	
16	6-Mar-2009	7	Updated SOT-223 mechanical data



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